

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 800 \text{ V}$$

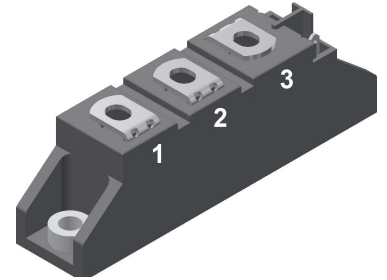
$$I_{TAV} = 60 \text{ A}$$

$$V_T = 1.24 \text{ V}$$

Phase leg

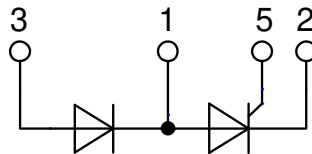
Part number

MCD56-08io8B



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			900	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			800	V	
I_{RD}	reverse current, drain current	$V_{R/D} = 800 V$	$T_{VJ} = 25^{\circ}C$		200	μA	
		$V_{R/D} = 800 V$	$T_{VJ} = 125^{\circ}C$		5	mA	
V_T	forward voltage drop	$I_T = 100 A$	$T_{VJ} = 25^{\circ}C$		1.26	V	
		$I_T = 200 A$			1.57	V	
		$I_T = 100 A$	$T_{VJ} = 125^{\circ}C$		1.24	V	
		$I_T = 200 A$			1.62	V	
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$		60	A	
$I_{T(RMS)}$	RMS forward current	180° sine			94	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.85	V	
r_T	slope resistance				3.7	m Ω	
R_{thJC}	thermal resistance junction to case				0.45	K/W	
R_{thCH}	thermal resistance case to heatsink			0.2		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		222	W	
I_{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		1.50	kA	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		1.62	kA	
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 125^{\circ}C$		1.28	kA	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		1.38	kA	
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		11.3	kA ² s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		10.9	kA ² s	
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 125^{\circ}C$		8.13	kA ² s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		7.87	kA ² s	
C_J	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		74	pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
P_{GAV}	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C$; f = 50 Hz	repetitive, $I_T = 150 A$		150	A/ μs	
		$t_p = 200 \mu s$; $di_G/dt = 0.45 A/\mu s$; $I_G = 0.45 A$; $V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 60 A$		500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}C$		1000	V/ μs	
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.5	V	
			$T_{VJ} = -40^{\circ}C$		1.6	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		100	mA	
			$T_{VJ} = -40^{\circ}C$		200	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.2	V	
I_{GD}	gate non-trigger current				10	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		450	mA	
		$I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$					
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^{\circ}C$		2	μs	
t_q	turn-off time	$V_R = 100 V$; $I_T = 150 A$; $V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$	$T_{VJ} = 100^{\circ}C$		150	μs	



Package TO-240AA				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			200	A	
T_{VJ}	virtual junction temperature		-40		125	°C	
T_{op}	operation temperature		-40		100	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					81	g	
M_D	mounting torque		2.5		4	Nm	
M_T	terminal torque		2.5		4	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
V_{ISOL}	isolation voltage	t = 1 second		4800		V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V	



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD56-08io8B	MCD56-08io8B	Box	36	457698

Similar Part	Package	Voltage class
MCMA65PD1200TB	TO-240AA-1B	1200
MCMA85PD1200TB	TO-240AA-1B	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}C$



Thyristor

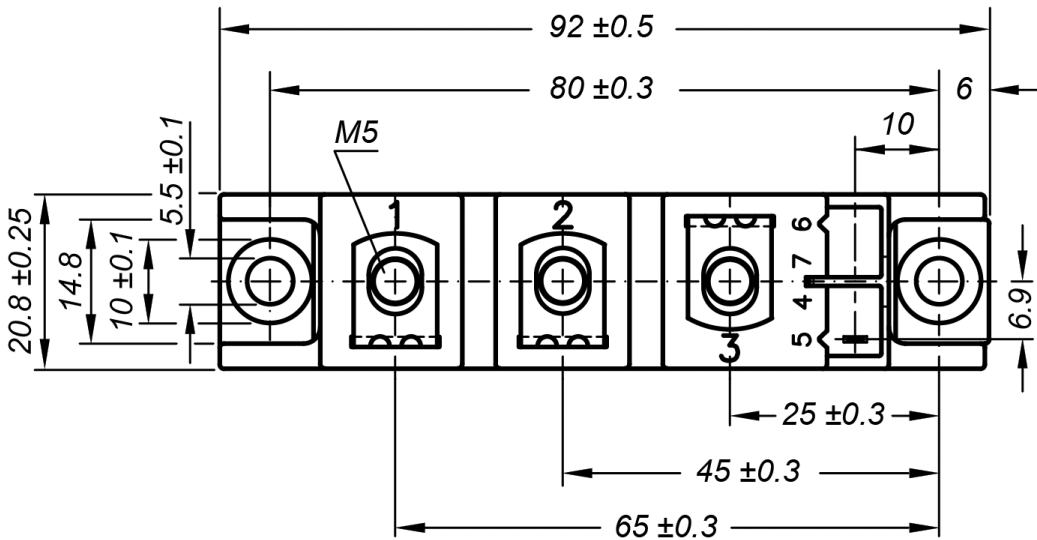
$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	2.5	mΩ



Outlines TO-240AA

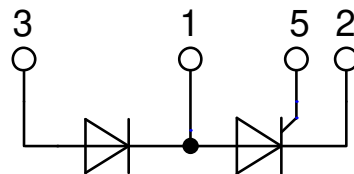


General tolerance: DIN ISO 2768 class „c“



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751





Thyristor

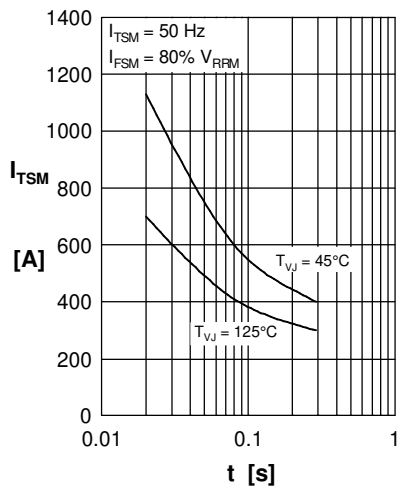


Fig. 1 Surge overload current I_{TSM} , I_{FSM} : Crest value, t : duration

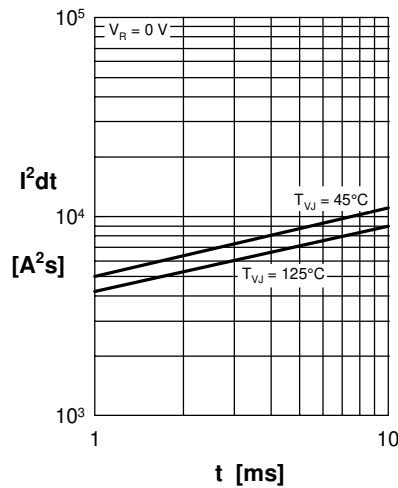


Fig. 2 I^2dt versus time (1-10 ms)

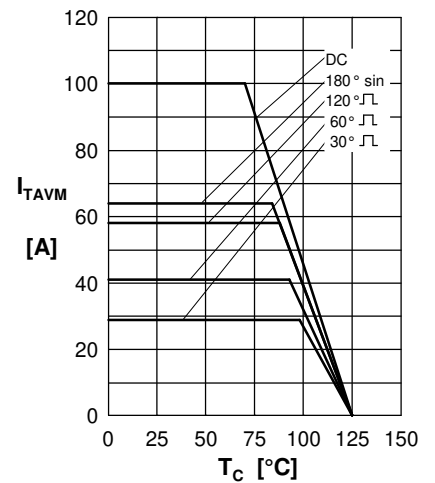


Fig. 3 Max. forward current at case temperature

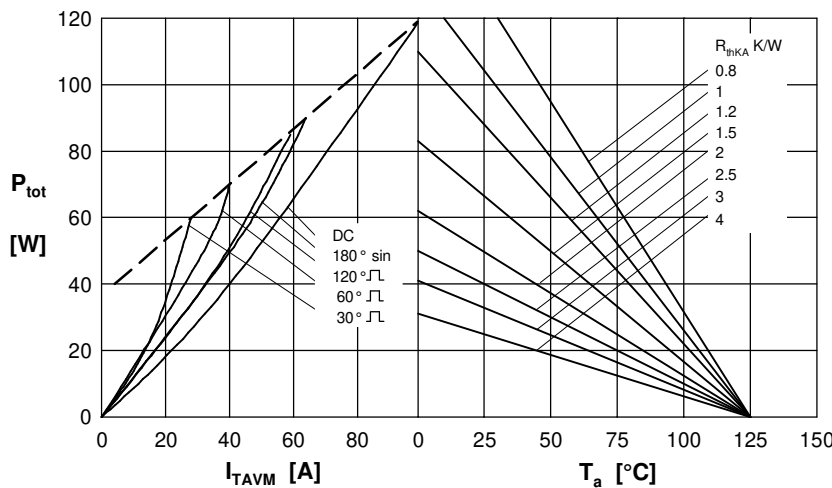


Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)

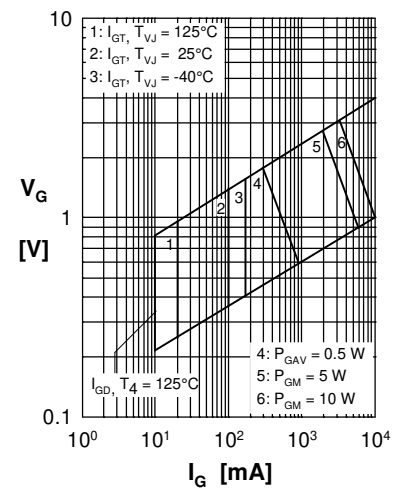


Fig. 5 Gate trigger characteristics

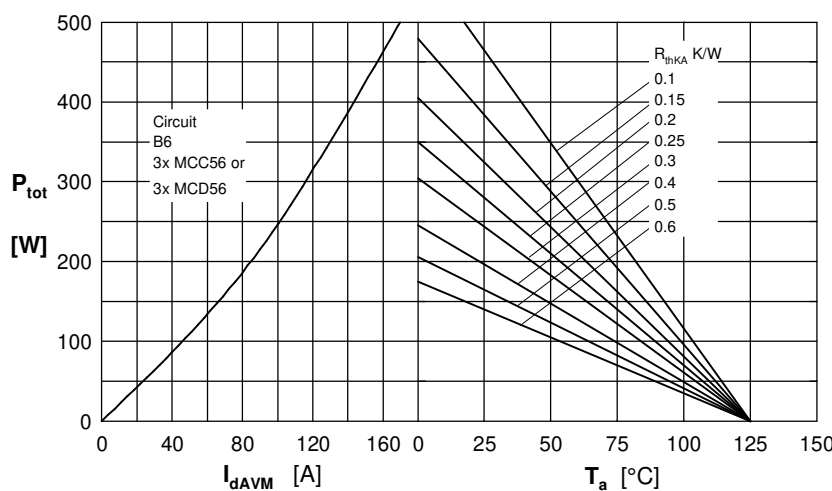


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

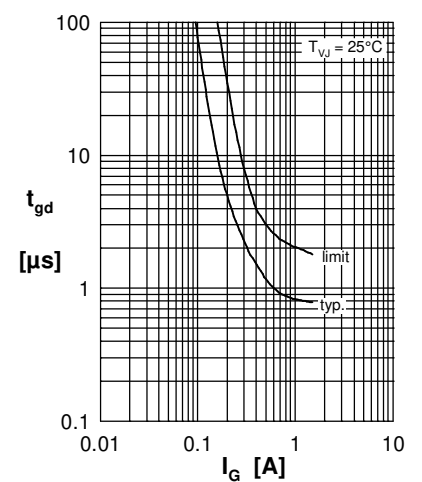


Fig. 7 Gate trigger delay time



Rectifier



Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature



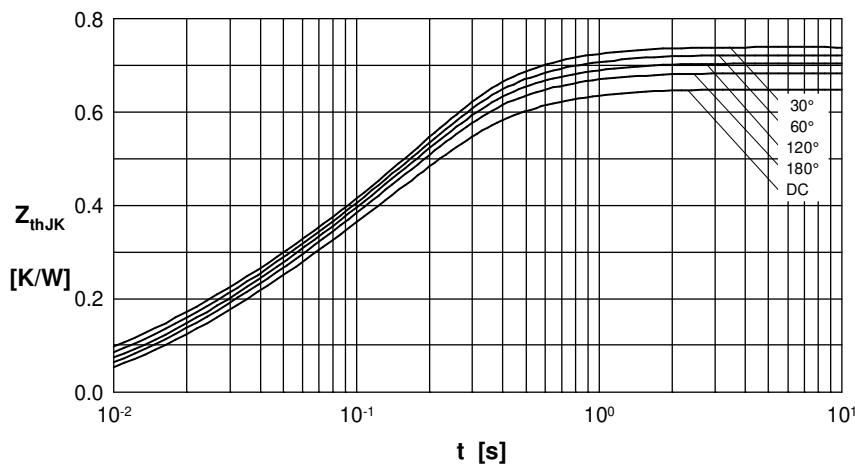
R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.450
180°	0.470
120°	0.490
60°	0.505
30°	0.520

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750

Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)



R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.650
180°	0.670
120°	0.690
60°	0.705
30°	0.720

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750
4	0.200	0.6700

Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)